



ISL9V3040D3S

Preliminary

Insulated Gate Bipolar Transistor

300mJ, 400V, N-CHANNEL
IGNITION IGBT

DESCRIPTION

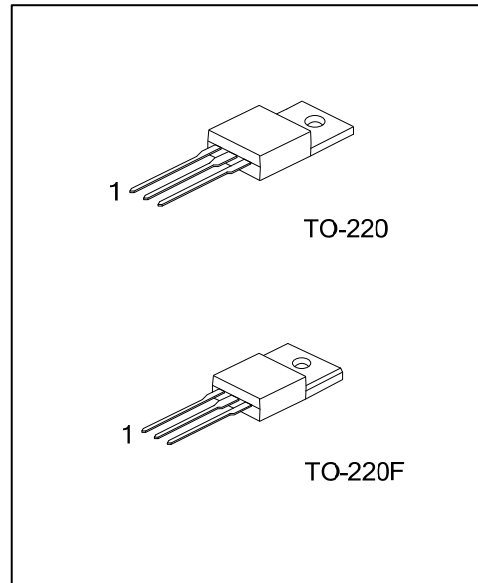
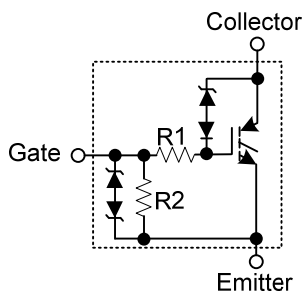
The UTC **ISL9V3040D3S** is an N-channel ignition Insulated Gate Bipolar Transistor. It uses UTC's advanced technology to provide customers with outstanding SCIS capability.

The UTC **ISL9V3040D3S** is suitable for Coil -On plug applications and Automotive Ignition Coil driver circuits, etc.

FEATURES

- * Outstanding SCIS capability
- * Logic level gate drive

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
ISL9V3040D3SL-TA3-T	ISL9V3040D3SG-TA3-T	TO-220	G	C	E	Tube
ISL9V3040D3SL-TF3-T	ISL9V3040D3SG-TF3-T	TO-220F	G	C	E	Tube

Note: Pin Assignment: G: Gate C: Collector E: Emitter

ISL9V3040D3SL-TA3-T	(1)Packing Type	(1) T: Tube
	(2)Package Type	(2) TA3: TO-220, TF3: TO-220F
	(3)Lead Free	(3) L: Lead Free, G: Halogen Free

MARKING INFORMATION

PACKAGE	MARKING
TO-220 TO-220F	

■ ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector to Emitter Breakdown Voltage		BV_{CER}	510	V
Emitter to Collector Voltage Reverse Battery Condition		BV_{ECS}	30	V
At Starting	$T_J=25^\circ\text{C}$, $I_{\text{SCIS}}=14.2\text{A}$, $L=3.0\text{mHy}$	E_{SCIS}	300	mJ
	$T_J=150^\circ\text{C}$, $I_{\text{SCIS}}=10.6\text{A}$, $L=3.0\text{mHy}$		170	mJ
Continuous Collector Current	$T_C=25^\circ\text{C}$	I_C	21	A
	$T_C=110^\circ\text{C}$		17	A
Gate to Emitter Voltage Continuous		V_{GEM}	± 10	V
Power Dissipation Total at $T_C=25^\circ\text{C}$	TO-220	P_D	125	W
	TO-220F		41.6	
Power Dissipation Derating $T_C>25^\circ\text{C}$	TO-220		1	W/ $^\circ\text{C}$
	TO-220F		0.332	
Electrostatic Discharge Voltage at 100pF, 1500 Ω		ESD	4	kV
Junction Temperature		T_J	-40~175	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-40~175	$^\circ\text{C}$

Note: Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Case	TO-220	θ_{JC}	1.0	$^\circ\text{C/W}$
	TO-220F		3.0	

■ ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off State Characteristics						
Collector to Emitter Breakdown Voltage	BV_{CER}	$I_C=2\text{mA}$, $V_{\text{GE}}=0\text{V}$, $R_G=1\text{K}\Omega$, $T_J=-40\sim 150^\circ\text{C}$	310		510	V
Collector to Emitter to Breakdown Voltage	BV_{CES}	$I_C=10\text{mA}$, $V_{\text{GE}}=0\text{V}$, $R_G=0$, $T_J=-40\sim 150^\circ\text{C}$	340		560	V
Emitter to Collector Breakdown Voltage	BV_{ECS}	$I_C=-75\text{mA}$, $V_{\text{GE}}=0\text{V}$, $T_C=25^\circ\text{C}$	30			V
Gate to Emitter Breakdown Voltage	BV_{GES}	$I_{\text{GES}}=\pm 2\text{mA}$	± 12	± 14		V
Collector to Emitter Leakage Current	I_{CER}	$V_{\text{CER}}=250\text{V}$, $R_G=1\text{K}\Omega$	$T_C=25^\circ\text{C}$		25	μA
			$T_C=150^\circ\text{C}$		1	mA
Emitter to Collector Leakage Current	I_{ECS}	$V_{\text{EC}}=24\text{V}$	$T_C=25^\circ\text{C}$		1	mA
			$T_C=150^\circ\text{C}$		40	mA
Series Gate Resistance	R_1			70		Ω
Gate to Emitter Resistance	R_2		10K		26K	Ω
On State Characteristics						
Collector to Emitter Saturation Voltage	$V_{\text{CE(SAT)}}$	$I_C=6\text{A}$, $V_{\text{GE}}=4\text{V}$	$T_C=25^\circ\text{C}$	1.25	1.60	V
		$I_C=10\text{A}$, $V_{\text{GE}}=4.5\text{V}$	$T_C=150^\circ\text{C}$	1.40	1.80	V
		$I_C=15\text{A}$, $V_{\text{GE}}=4.5\text{V}$	$T_C=150^\circ\text{C}$	1.90	2.20	V
Dynamic Characteristics						
Gate Charge	$Q_{\text{G(ON)}}$	$I_C=10\text{A}$, $V_{\text{CE}}=12\text{V}$, $V_{\text{GE}}=5\text{V}$		17		nC
Gate to Emitter Threshold Voltage	$V_{\text{GE(TH)}}$	$I_C=1.0\text{mA}$, $V_{\text{CE}}=V_{\text{GE}}$	1.3		2.2	V
Gate to Emitter Plateau Voltage	V_{GEP}	$I_C=10\text{mA}$, $V_{\text{CE}}=12\text{V}$		3.0		V
Switching Characteristics						
Current Turn-On Delay Time-Resistive	$t_{\text{d(ON)R}}$	$V_{\text{CE}}=14\text{V}$, $R_L=1\Omega$, $V_{\text{GE}}=5\text{V}$, $R_G=1\text{K}\Omega$, $T_J=25^\circ\text{C}$		0.48	4	μs
Current Rise Time-Resistive	t_{r}			2.1	7	μs
Current Turn-Off Delay Time-Inductive	$t_{\text{d(OFF)L}}$			1.4	15	μs
Current Fall Time Inductive	t_{fL}			2.2	15	μs
Self Clamped Inductive Switching	SCIS	$T_J=25^\circ\text{C}$, $L=3.0\text{mHy}$, $R_G=1\text{K}\Omega$,			300	mJ

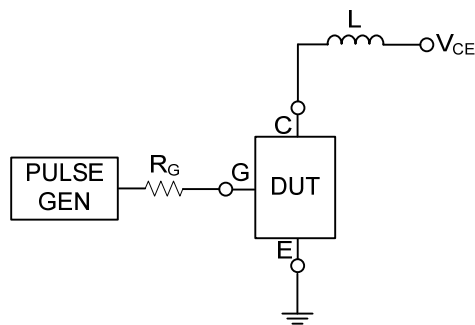
ISL9V3040D3S

Preliminary

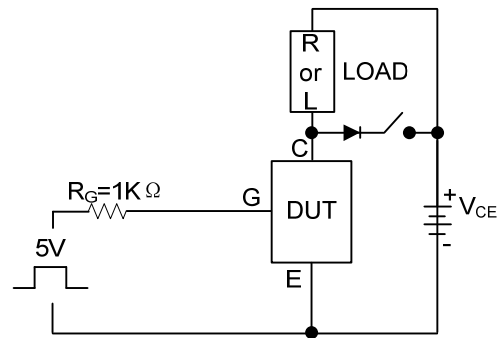
Insulated Gate Bipolar Transistor

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
		$V_{GE}=5V$				

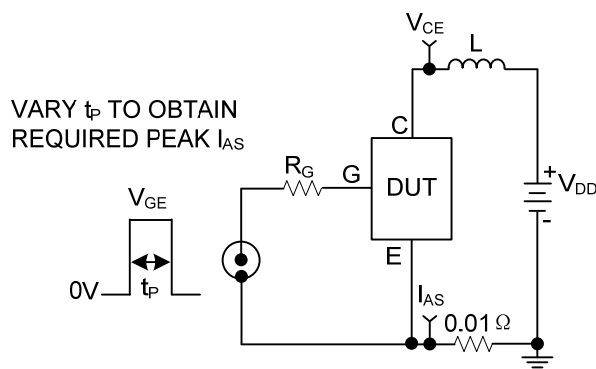
■ TEST CIRCUIT AND WAVEFORMS



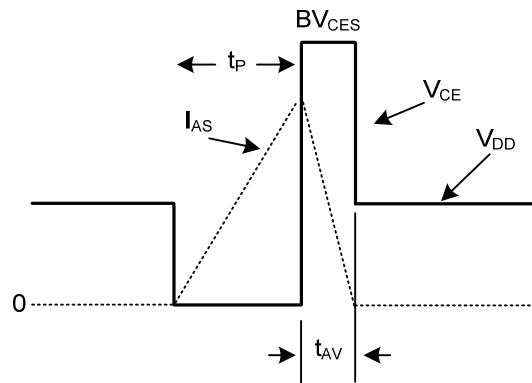
Inductive Switching Test Circuit



t_{ON} and t_{OFF} Switching Test Circuit



Energy Test Circuit



Energy Waveforms

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